

www.vishay.com Vishay Siliconix

# N-Channel 40 V (D-S) MOSFET



PRODUCT SUMMARY					
V <sub>DS</sub> (V)	40				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 10 \text{ V}$	0.00099				
$R_{DS(on)}$ max. ( $\Omega$ ) at $V_{GS} = 4.5 \text{ V}$	0.00136				
Q <sub>g</sub> typ. (nC)	182				
I <sub>D</sub> (A) <sup>d</sup>	200				
Configuration	Single				

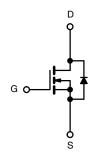
### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- Maximum 175 °C junction temperature
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



### **APPLICATIONS**

- Power supply
  - Secondary synchronous rectification
- DC/DC converter
- Power tools
- · Motor drive switch
- DC/AC inverter
- · Battery management
- OR-ing



N-Channel MOSFET

ORDERING INFORMATION	
Package	D <sup>2</sup> PAK (TO-263-7L)
Lead (Pb)-free and halogen-free	SUM40014M-GE3

ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-source voltage	V <sub>DS</sub>	40	V			
Gate-source voltage	V <sub>GS</sub>	± 20				
Continuous drain current (T <sub>J</sub> = 150 °C)	T <sub>C</sub> = 25 °C		200 <sup>d</sup>			
	T <sub>C</sub> = 70 °C	─ I <sub>D</sub>	200 <sup>d</sup>			
Pulsed drain current (t = 100 μs)	I <sub>DM</sub>	400	Α			
Avalanche current		I <sub>AS</sub>	70			
Single avalanche energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	245	mJ		
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	375 <sup>b</sup>	W		
	T <sub>C</sub> = 125 °C	P <sub>D</sub>	125 <sup>b</sup>			
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-ambient (PCB mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-case (drain)	$R_{thJC}$	0.4			

#### Notes

- a. Duty cycle ≤ 1 %
- b. See SOA curve for voltage derating
- c. When mounted on 1" square PCB (FR4 material)
- d. Package limited



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<b>SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}$	40	-	-	V	
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.1	-	2.4	V	
Gate-body leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 250	nA	
		$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	1		
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 40 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 125 \text{ °C}$	-	-	150	μA	
		V <sub>DS</sub> = 40 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 175 °C	-	-	5	mA	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>DS</sub> ≥ 10 V, V <sub>GS</sub> = 10 V	100	-	-	Α	
Drain-source on-state resistance a	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A	-	0.00082	0.00099	Ω	
Drain-source on-state resistance "	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 15 \text{ A}$	-	0.00113	0.00136		
Forward transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A	_	140	-	S	
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>		-	15 780	-	pF	
Output capacitance	Coss	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	2280	-		
Reverse transfer capacitance	C <sub>rss</sub>		-	90	-		
Total gate charge <sup>c</sup>	Qg		-	182	275		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 20 \text{ A}$	-	41	-	nC	
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>		-	9	-		
Gate resistance	R <sub>g</sub>	f = 1 MHz	0.5	2.4	4.8	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>		_	20	40		
Rise time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = 50 \text{ V}, R_L = 5 \Omega$	-	10	20	ns	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 10 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$	-	100	200		
Fall time <sup>c</sup>	t <sub>f</sub>		-	35	70		
Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (T <sub>C</sub> = 25 °C)							
Pulsed current (t = 100 μs)	I <sub>SM</sub>		-	-	600	Α	
Forward voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 V	-	0.72	1.5	V	
Reverse recovery time	t <sub>rr</sub>		-	55	80	ns	
Peak reverse recovery charge	I <sub>RM(REC)</sub>	I <sub>F</sub> = 20 A, di/dt = 100 A/μs	-	2.2	5	Α	
Reverse recovery charge	Q <sub>rr</sub>		-	0.065	0.13	μC	

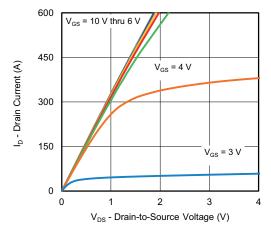
## Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

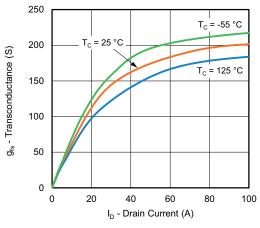
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



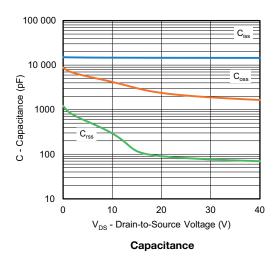
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)

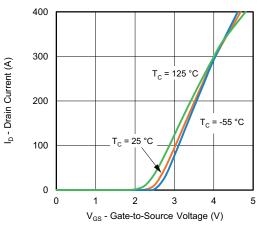


### **Output Characteristics**

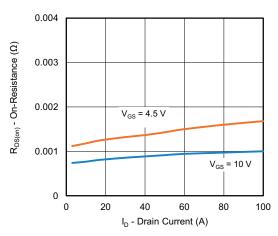


### Transconductance

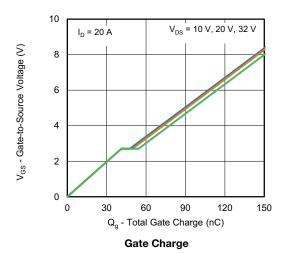




### **Transfer Characteristics**

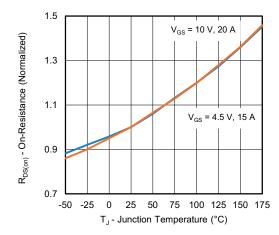


**On-Resistance vs. Drain Current** 

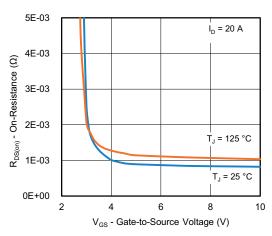




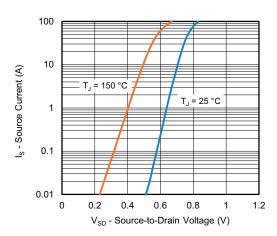
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



On-Resistance vs. Junction Temperature



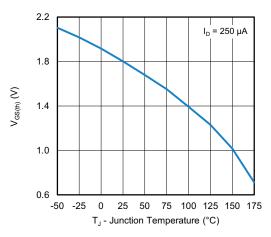
On-Resistance vs. Gate-to-Source Voltage



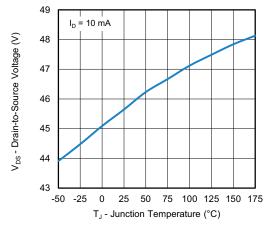
**Source Drain Diode Forward Voltage** 

### Note

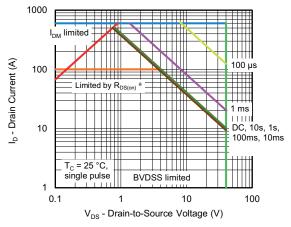
a.  $V_{GS} > minimum \ V_{GS}$  at which  $R_{DS(on)}$  is specified



**Threshold Voltage** 



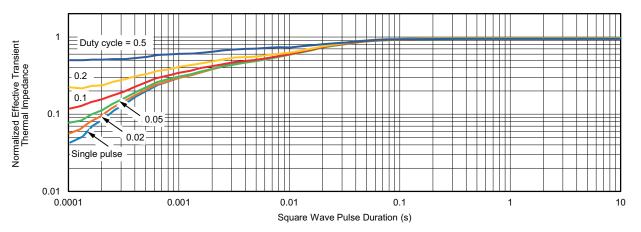
**Drain Source Breakdown vs. Junction Temperature** 



Safe Operating Area



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

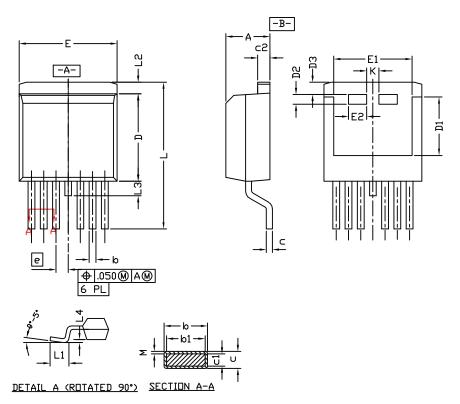
- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg277646">www.vishay.com/ppg277646</a>.

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# D<sup>2</sup>PAK (TO-263-7L) Case Outline



### Notes

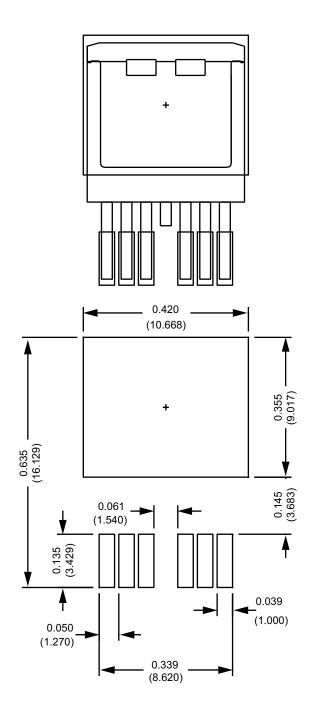
- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin to pin coplanarity max. 4 mils.
- 4. Lead thickness 25 mils.
- 5. For SUM part numbers lead thickness is 24 mils to 29 mils.
- 6. For reference only.
- 7. Use inches as the primary measurement.
- 8. This feature is only for SUM.

	INCHES		MILLIN	METERS
DIM.	MIN.	MAX.	MIN.	MAX.
Α	0.160	0.190	4.064	4.826
b	0.020	0.039	0.508	0.990
b1	0.020	0.035	0.508	0.889
b2	0.045	0.055	1.143	1.397
c* SUB	0.012	0.018	0.305	0.457
c* SUM	0.022	0.028	0.559	0.711
c1	0.018	0.025	0.457	0.635
c2	0.045	0.055	1.143	1.397
D	0.340	0.380	8.636	9.652
D1	0.220	0.240	5.588	6.096
D2	0.038	0.042	0.965	1.067
D3	0.045	0.055	1.143	1.397
Е	0.380	0.410	9.652	10.414
E1	0.245	-	6.223	-
E2	0.072	0.078	1.829	1.981
е	0.050 BSC		1.27 BSC	
K	0.045	0.055	1.143	1.397
L	0.575	0.625	14.605	15.875
L1	0.090	0.110	2.286	2.794
L2	0.040	0.055	1.016	1.397
L3	0.050	0.070	1.270	1.778
L4	0.010	BSC	0.254 BSC	
М	-	0.002	-	0.050
ECN: T13-0709-Rev. B, 30-Sep-13 DWG: 6006				

Revision: 30-Sep-13 Document Number: 63782



# Recommended Land Pattern D<sup>2</sup>PAK (TO-263-7L)





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